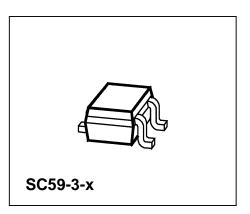


# Low Power Hall Switch

TLE 4913

## Features

- Micro power design
- 2.4 V to 5.5 V battery operation
- High sensitivity and high stability of the magnetic switching points
- High resistance to mechanical stress
- Digital output signal
- Switching for both poles of a magnet (omnipolar)
- Not suitable for automotive application



### **Functional Description**

The TLE4913 is an Integrated Hall-Effect Sensor designed specifically to meet the requirements of low-power devices. e.g. as an On/Off switch in Cellular Flip-Phones, with battery operating voltages of 2.4V - 5.5V.

Precise magnetic switching points and high temperature stability are achieved through the unique design of the internal circuit.

An onboard clock scheme is used to reduce the average operating current of the IC.

During the operate phase the IC compares the actual magnetic field detected with the internally compensated switching points. The output Q is switched at the end of each operating phase.

During the Stand-by phase the output stage is latched and the current consumption of the device reduced to some  $\mu A$ .

The IC switching behaviour is Omnipolar, i.e. it can be switched on with either the North or South pole of a magnet.

Туре	Marking	Ordering Code	Package
TLE 4913	13s 013	SP000013490	SC 59-3-x



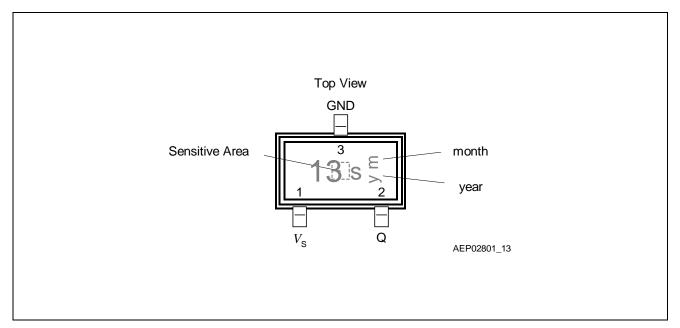


Figure 1 Pin Configuration (top view)

# **Pin Definitions and Functions**

Pin	Symbol	Function
1	Vs	Supply Voltage
2	Q	Open Drain Input
3	Gnd	Ground



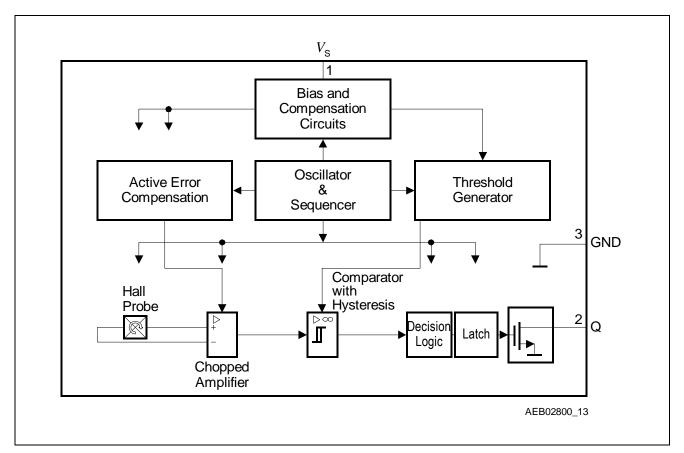


Figure 2 Block Diagram

### **Circuit Description**

The Low Power Hall IC Switch comprises a Hall probe, bias generator, compensation circuits, oscillator, output latch and an n-channel open drain output transistor.

The bias generator provides currents for the Hall probe and the active circuits. Compensation circuits stabilize the temperature behavior and reduce technology variations.

The Active Error Compensation rejects offsets in signal stages and the influence of mechanical stress to the Hall probe caused by molding and soldering processes and other thermal stresses in the package. This chopper technique together with the threshold generator and the comparator ensures high accurate magnetic switching points.

Very low power consumption is achieved with a timing scheme controlled by an oscillator and a sequencer. This circuitry activates the sensor for 50  $\mu$ s (typical operating time) sets the output state after sequential questioning of the switch points and latches it with the beginning of the following standby phase (max. 200 ms). In the standby phase the average current is reduced to typical 4  $\mu$ A. Because of the long standby time compared to the operating time the overall averaged current is only slightly higher than the standby current.

The output transistor can sink up to 1 mA with a maximal saturation voltage  $V_{QSAT}$ .



Parameter	Symbol	Limi	t Values	Unit	Notes
		min.	max.		
Supply Voltage	Vs	- 0.3	5.5	V	
Supply Current	Is	- 1	2.5	mA	
Output Voltage	$V_{Q}$	- 0.3	5.5	V	
Output Current	IQ	- 1	2	mA	
Junction temperature	Ti	- 40	150	°C	
Storage temperature	Ts	- 40	150	°C	
Magnetic Flux Density	В	-	unlimited	mT	
Thermal Resistance P-SC59-3-x	$R_{ m th JA}$	-	35	K/W	

### Absolute Maximum Ratings

Note: Stresses above those listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### ESD Protection

Human Body Model (HBM) tests according to: EOS/ESD Association Standard S5.1-1993 and Mil. Std. 883D method 3015.7

Parameter	Symbol	Limi	t Values	Unit	Notes	
		Min.	Max.			
ESD Voltage	V <sub>ESD</sub>		± 4	kV	$R = 1.5 \text{ k}\Omega,$ C = 100  pF;	
					T = 25  °C	



### **Operating Range**

Parameter	Symbol	Limit Values			Unit	Notes
		Min.	typ.	max.		
Supply voltage	Vs	2.4	2.7	5.5	V	1)
Output voltage	$V_{Q}$	- 0.3	2.7	5.5	V	
Ambient Temperature	T <sub>A</sub>	- 40	25	85	°C	

 $^{\rm 1)}$  A Ceramic Bypass Capacitor of 100 nF at  $V_{\rm S}$  to GND is highly recommended.

### **AC/DC Characteristics**

Parameter	Symbol	Limit Values			Unit	Notes
		Min. typ.		Max.		
Averaged Supply Current	I <sub>SAVG</sub>	1	4	20	μA	
Averaged Supply Current during Operating Time	ISOPAVG	0.5	1.1	2.5	mA	
Transient Peak Supply Current during Operating Time	I <sub>SOPT</sub>	_	-	2.5	mA	<i>t</i> < 100 ns
Supply Current during Standby Time	I <sub>SSTB</sub>	1	3.5	20	μA	
Output Saturation Voltage	$V_{QSAT}$	-	0.13	0.4	V	$I_Q = 1 \text{ mA}$
Output Leakage Current		-	0.01	1	μA	
Output Rise Time	<i>t</i> r	-	0.5	1	μs	$R_{\rm L} = 2.7 \text{ k}\Omega;$ $C_{\rm L} = 10 \text{ pF}$
Output Fall Time	t <sub>f</sub>	-	0.1	1	μs	$R_{\rm L} = 2.7 \text{ k}\Omega;$ $C_{\rm L} = 10 \text{ pF}$
Operating Time	<i>t</i> <sub>op</sub>	15	50	93 <sup>1) 2)</sup>	μs	
Standby Time	t <sub>stb</sub>	-	130	240 <sup>3)</sup>	ms	
Duty Cycle	$t_{\rm op}$ / $t_{\rm stb}$	-	0.039	_	%	
Start-up Time of IC	<i>t</i> <sub>stu</sub>	-	6	12	μs	4)

<sup>1)</sup> for V<sub>S</sub>=3.5V the max. Operating Time  $t_{op max}$  = 85µs

<sup>2)</sup> includes the Start-up Time  $t_{stu}$ 

<sup>3)</sup> for V<sub>S</sub>=3.5V the max. Standby Time  $t_{stb max}$  = 220ms <sup>4)</sup> initial power on time. V<sub>S</sub> must be applied in this time ( typ. 6µs to max. 12µs ) to get already a valid output state after the first operating phase (typ. 56µs). For rise times of V<sub>S</sub> > 12µs, the output state is valid after the second operating phase (includes one standby phase), e.g. happens only when the battery in flip phones is changed.



## Magnetic Characteristics

Parameter	Symbol	Limit Values			Unit	Notes
		min.	typ.	max.		
Operate Points	B <sub>OPS</sub>	2	3.5	5	mT	1)
(Output on)	BOPN	- 5	- 3.5	- 2	mT	
Release Points	B <sub>RPS</sub>	1,2	2.7	4.2	mT	1)
(Output off)	B <sub>RPN</sub>	- 4.2	- 2.6	- 1,2	mT	
Hysteresis	B <sub>HYS</sub>	0.2	0.8	1,6	mT	

<sup>1)</sup> Positive magnetic fields are related to the approach of a magnetic south pole to the branded side of package

Note: The listed AC/DC and magnetic characteristics are ensured over the operating range of the integrated circuit. Typical characteristics specify mean values expected over the production spread. If not other specified, typical characteristics apply at  $T_j = 25$  °C and  $V_S = 2.7$  V



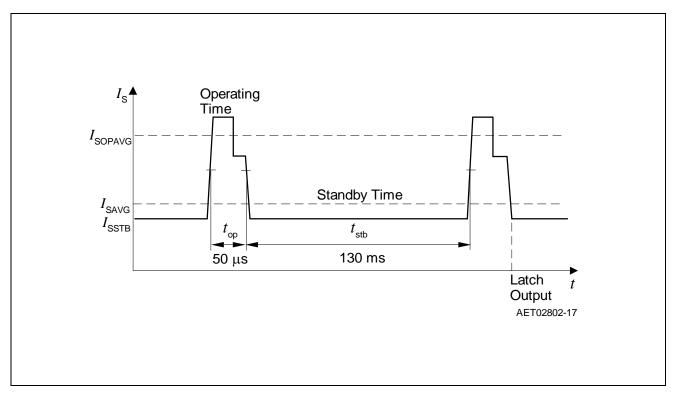
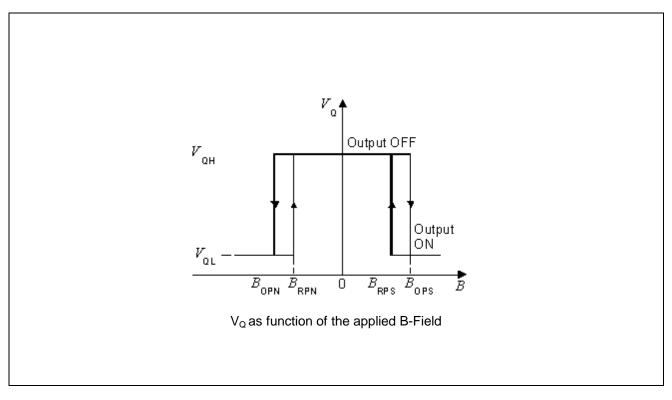


Figure 3 Timing Diagram



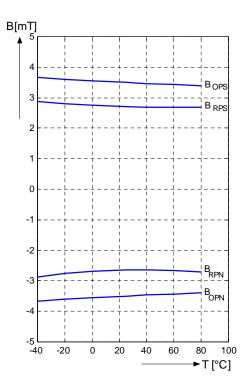
# Figure 4 Output – Signal TLE 4913

Data Sheet

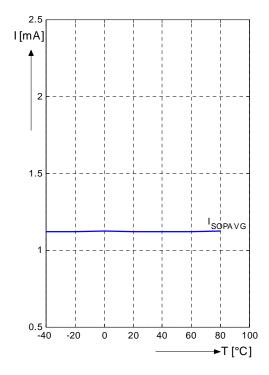


## All curves reflect typical values at the given parameters for $T_A$ in °C and $V_S$ in V.

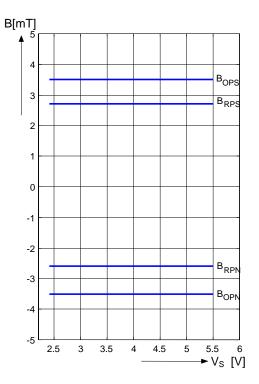
### Magnetic Switching Points versus Temperature (V<sub>s</sub>=2.7V)



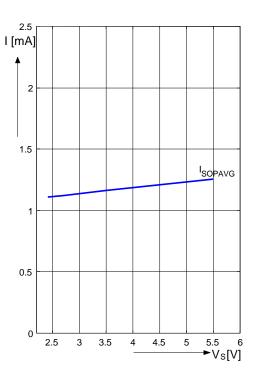
# Supply current $I_{SOPAVG}$ during Operating Time versus Temperature (V<sub>S</sub>=2.7V)



# Magnetic Switching Points versus Supply Voltage $V_S$ (T<sub>A</sub>=20°C)



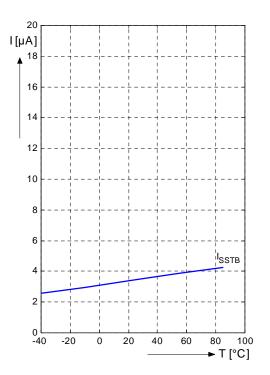
Supply current I<sub>SOPAVG</sub> during Operating Time versus Supply Voltage V<sub>S</sub> (T<sub>A</sub>=20°C)



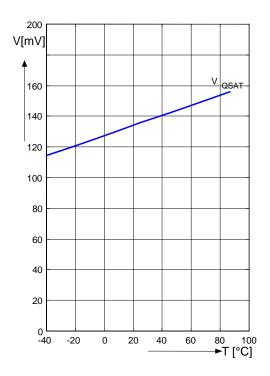
Data Sheet



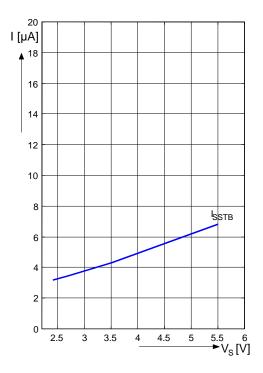
### Supply current I<sub>SSTB</sub> during Standby Time versus Temperature (V<sub>S</sub>=2.7V)



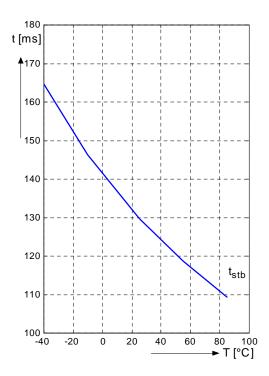
Output Saturation voltage  $V_{QSAT}$  versus Temperature ( $I_Q=1mA$ )



### Supply current I<sub>SSTB</sub> during Standby Time versus Supply Voltage V<sub>S</sub> (T<sub>A</sub>=20°C)



Standby Time  $t_{stb}$  versus Temperature (V<sub>S</sub> = 2.7V)



Data Sheet



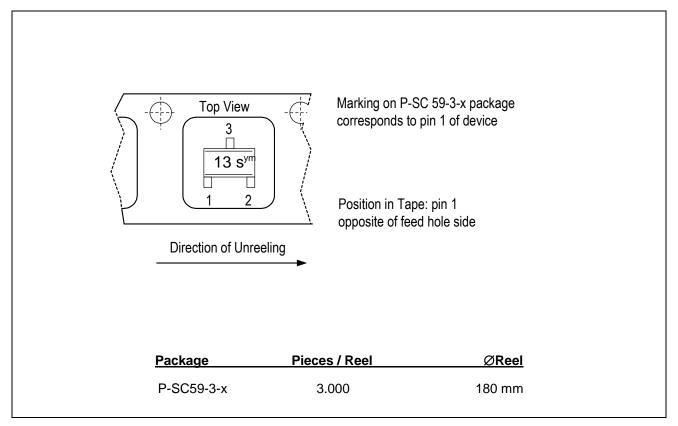


Figure 5 Marking and Tape Loading Orientation

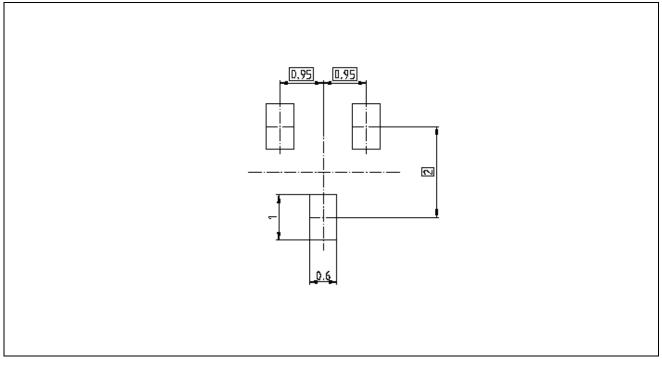
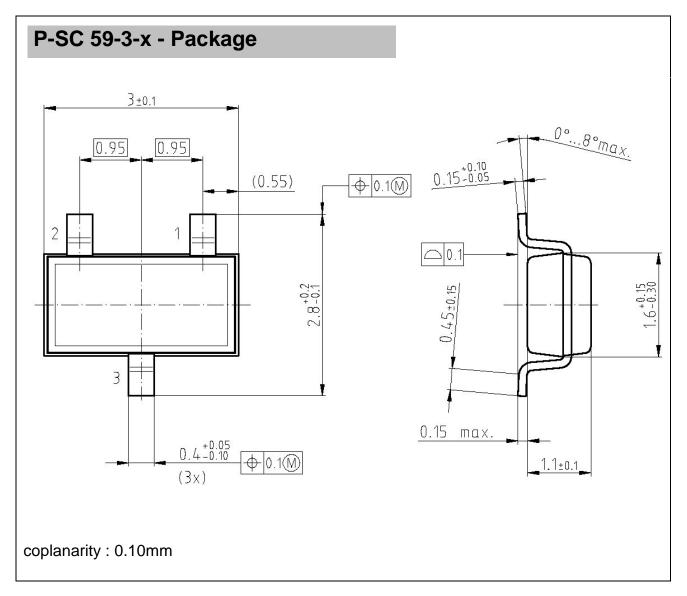


Figure 6 Foot Print Reflow Soldering

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## **Package Dimensions**



### Sorts of Packing

Package outlines for tubes, trays etc. are contained in our Data Book "Package Information".

SMD = Surface Mounted Device

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TLE4913		
<b>Revision His</b>	tory: 2019-05-14	V 2.3
Previous Vers	ion: 2003-07-16 and 2004-03-09	
Page	Subjects (major changes since last revision)	
4	ESD Level adapted to ±4 kV	
1	Change of Ordering Code from Q62705K 619 into SP000013490	

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